

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

APR 07 2004

Complete if Known

Application Number	10/690,290				
Filing Date	October 21, 2003				
First Named Inventor	Yuji HORI				
Art Unit	2814				
Examiner Name	Ngan V. Ngo				
Confirmation No.	4572				
Sheet	1	of	1	Attorney Docket No.	782_202 DIV2

U.S. PATENT DOCUMENTS

Exam. Initial		Document Number	Date	Name	Our Docket No.	Class	Sub Class	Filing Date
YH	AA*	5,990,495	11-23-1999	Ohba, Yasuo				
YH	AB*	6,064,082	05-16-2000	Kawai et al.				
YH	AC*	5,810,925	09-22-1998	Tadatomo et al.				

U.S. COPENDING APPLICATIONS

Exam. Initial		Application/ Publication Number	Filing/ Publication Date	Inventor Name	Our Docket No.	Class	Sub Class

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Sub Class	Translation	Abstract
YH	AD	WO 98/35388	08-13-1998	US				

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages etc.)

YH	AE	M.A. Khan et al., "High Electron Mobility Transistor Based on a GaN-Al _x Ga _{1-x} N Heterojunction," Applied Physics Letters, 30 August 1993, USA, Vol. 63, No. 9, pages 1214-1215, XP002269124
YH	AF	P. Kung et al., "High Quality AlN and GaN Epilayers Grown on (pp.1) Sapphire, (100) and (111) Silicon Substrates," Applied Physics Letters, American Institute of Physics, NY, US, Vol. 66, No. 22, 29 May 1995, pages 2958-2960, XP000507525

Examiner:

M. H. Ngo

Date Considered:

06/04/04

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

*In accordance with the Notice dated July 11, 2003 on the PTO website, we are not enclosing copies of any of the U.S. references listed above.